

The ARF469A and ARF469B comprise a symmetric pair of common source RF power transistors designed for pushpull scientific, commercial, medical and industrial RF power amplifier applications up to 45 MHz. They have been optimized for both linear and high efficiency classes of operation.

• Specified 150 Volt, 40.68 MHz Characteristics:

Output Power = 350 Watts.

Gain = 16dB (Class AB)

Efficiency = 75% (Class C)

- Low Cost Common Source RF Package.
- Low Vth thermal coefficient.
- Low Thermal Resistance.
- Optimized SOA for Superior Ruggedness.

All Ratings: $T_{a} = 25^{\circ}$ C unless otherwise specified.

MAXIMUM RATINGS

Symbol	Parameter	Ratings	UNIT		
V _{DSS}	Drain-Source Voltage	500	Volts		
V _{DGO}	Drain-Gate Voltage	500			
I _D	Continuous Drain Current @ T _C = 25°C	30	Amps		
V _{GS}	Gate-Source Voltage	±30	Volts		
P _D	Total Power Dissipation @ T_{c} = 25°C	445	Watts		
R _{ejc}	Junction to Case	0.28	°C/W		
T_,T _{STG}	Operating and Storage Junction Temperature Range	-55 to 150	- °C		
Τ _L	Lead Temperature: 0.063" from Case for 10 Sec.	300			

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage (V_{GS} = 0V, I_{D} = 250 µA)	500			Volts
$R_{DS(ON)}$ Drain-Source On-State Resistance ⁽¹⁾ ($V_{GS} = 10V^{,I}I_{D} = 15A$)0.25		0.28	ohms		
	Zero Gate Voltage Drain Current (V_{DS} = 500V, V_{GS} = 0V)			25	
DSS	Zero Gate Voltage Drain Current (V_{DS} = 400V, V_{GS} = 0V, T_{C} = 125°C)			250	μA
I _{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 30V$, $V_{DS} = 0V$)			±100	nA
9 _{fs}	Forward Transconductance (V_{DS} = 25V, I_{D} = 6.5A)		8		mhos
V _{GS} (TH)	Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_{D} = 1mA$)	2		4	Volts

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

DYNAMIC CHARACTERISTICS

ARF469AG_BG

Symbol	Characteristic	Test Conditions	MIN	ТҮР	MAX	UNIT
C _{iss}	Input Capacitance	V _{GS} = 0V		2300		
C _{oss}	Output Capacitance	V _{DS} = 150V f = 1 MHz		250		pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 101112		125		

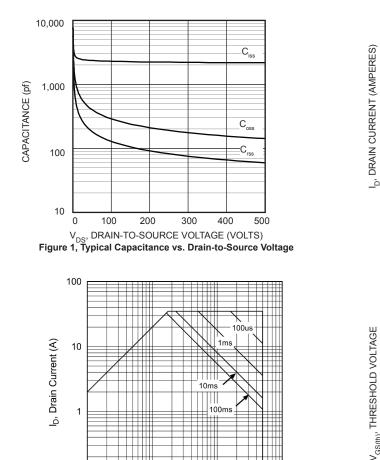
FUNCTIONAL CHARACTERISTICS

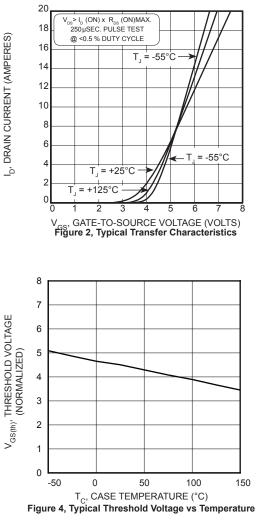
Symbol	Characteristic	Test Conditions	MIN	ТҮР	MAX	UNIT
G _{PS}	Common Source Amplifier Power Gain	f = 40.68 MHz	14	16		dB
η	Drain Efficiency	V _{GS} = 2.5V V _{DD} = 150V	70	75		%
Ψ	Electrical Ruggedness VSWR 10:1	P _{out} = 350W	No Deg	lo Degradation in Output Power		

(1) Pulse Test: Pulse width < 380μ S, Duty Cycle < 2%

Microsemi Reserves the right to change, without notice, the specifications and information contained herein.

TYPICAL PERFORMANCE CURVES





0.1

1

10

 V_{DS} , Drain-to-Source Voltage (V)

Figure 3, Typical Maximum Safe Operating Area

100

1000

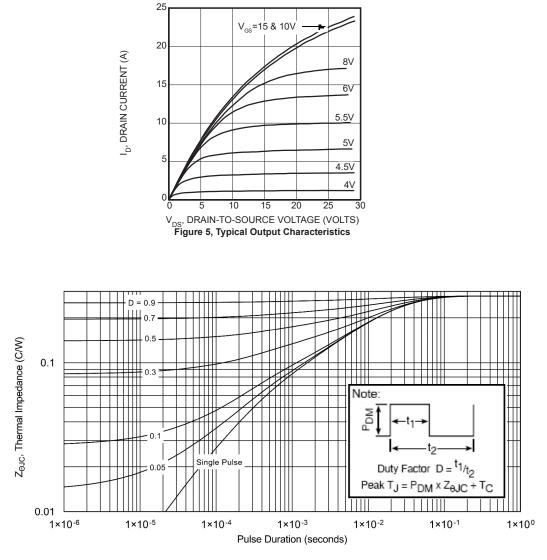
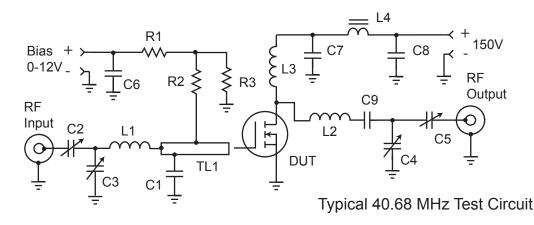


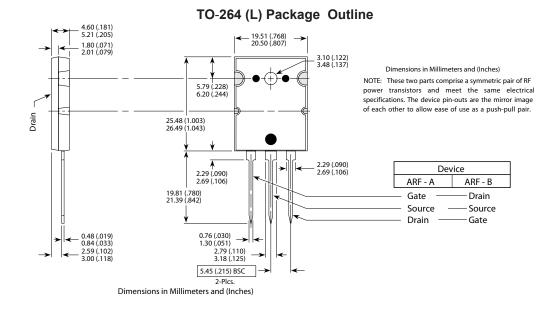
FIGURE 6, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

Freq. (MHz)	Z _{in} (Ω)	Ζ _{οι} (Ω)
2.0	18 - j 10.8	30 - j 1.5
13.5	1.3 - j 4.8	26- j 9.6
27.1	0.4- j 2.4	18 - j 13.1
40.7	0.2 - j 1.4	12 - j 12.4

Table 1 - Typical Class AB Large Signal Input - Output Impedance



C1 -- 2200pF ATC 700B C2-C5 -- Arco 465 Mica trimmer C6-C8 -- .1 μF 500V ceramic chip C9 -- 3x 2200 pF 500V chips COG L1 -- 4t #22 AWG .25"ID .25 "L ~87nH L2 -- 5t #16 AWG .312" ID .35"L ~176nH L3 -- 10t #24 AWG .25"ID ~.5µH L4 -- VK200-4B ferrite choke 3µH R1- R3 -- $1k\Omega 0.5\Omega$ Carbon TL1 -- 34Ω t-line 0.175" x 1" C1 .45" from gate pin. PCB -- 0.062" FR4, Er=4.7





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